

MGBR20V50 Preliminary DIODE

MOS GATED BARRIER RECTIFIER

■ DESCRIPTION

The UTC MGBR20V50 is a surface mount mos gated barrier rectifier, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed etc.

The UTC MGBR20V50 suitable for supply applications.

■ FEATURES

- * Very low forward voltage drop
- * High switching speed

■ SYMBOL

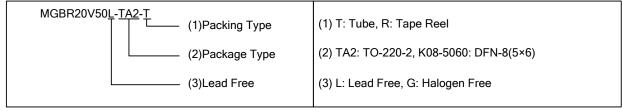


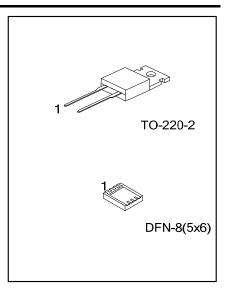


■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment							Doolsing		
Lead Free	Halogen Free	Package	1	2	З	4	5	6	7	8	Packing	
MGBR20V50L-TA2-T	MGBR20V50G-TA2-T	TO-220-2	Κ	Α	ı	-	1	ı	ı	-	Tube	
MGBR20V50L-K08-5060-R	MGBR20V50G-K08-5060-R	DFN-8(5×6)	Α	Α	Α	NC	Κ	Κ	Κ	Κ	Tape Reel	

Note: Pin Assignment: A: Anode, K: Cathode





■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
DC Blocking Voltage	V_{RM}	50	V
Working Peak Reverse Voltage	V_{RWM}	50	V
Peak Repetitive Reverse Voltage	V_{RRM}	50	V
Average Rectified Forward Current (Rated VR-20Khz Square Wave) - 50% Duty Cycle	Io	20	Α
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	250	Α
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	2	Α
Maximum Rate of Voltage Change (at Rated V _R)	dv/dt	10000	V/µS
Operating Junction Temperature	T_J	-65~+150	°C
Storage Junction Temperature	T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
lunation to Ambient	TO-220-2	0	60	00,000
Junction to Ambient	DFN-8(5×6)	θ _{JA}	72	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C unless otherwise specified)

PARAMETER	PARAMETER SYMBOL TEST CONDITIONS		MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.50mA	50			V
Forward Voltage	V_{FM}	I _F =20A, T _J =25°C			0.58	V
		I _F =20A, T _J =125°C			0.53	V
Reverse Current (Note 1)	DM	V _R =50V, T _J =25°C			500	μA
		V _R =50V, T _J =125°C			100	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

